

**UNIVERSITY OF CALIFORNIA**  
**College of Engineering**  
**Department of Electrical Engineering**  
**and Computer Sciences**

**B. E. BOSER**

**Final**  
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**EECS 240**  
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*Clearly **mark results** with box around. No credit for ambiguous solutions. Show derivations. Do all calculations on exam sheet and return exam sheet. Exam is "open book, open notes". Good luck!*

Device Parameters (all problems unless otherwise noted):

<b>C</b>	<b>NMOS/NPN</b>	<b>PMOS/PNP</b>
$C_{ox}$	2 fF/ $\mu\text{m}^2$	2 fF/ $\mu\text{m}^2$
$\mu$	$\mu_n = 500 \text{ cm}^2/\text{V-s}$	$\mu_p = 200 \text{ cm}^2/\text{V-s}$
$V_{TH}$	1 V	-1 V
$\lambda$ at $L = 1 \mu\text{m}$	0.1 $\text{V}^{-1}$	0.1 $\text{V}^{-1}$
$K_f$	$10^{-24} \text{ V}^2\text{F}$	$0.5 \times 10^{-24} \text{ V}^2\text{F}$
$C_{ol}$	0 fF/ $\mu\text{m}$	0 fF/ $\mu\text{m}$
$V_{BE(on)}$	0.7V	-0.7V
$V_{CE(sat)}$	200mV	-200mV
$r_b$	0 $\Omega$	0 $\Omega$
$\beta_f$	100	100

Assume square-law characteristics for the MOS devices.

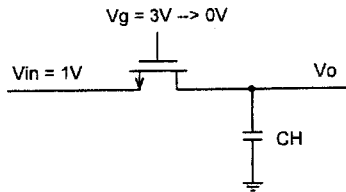
Name: \_\_\_\_\_ (1 point)

<b>Problem</b>	<b>Score</b>
1	
2	
3	
4	
<b>Total</b>	

## 1. MOS Sample & Hold

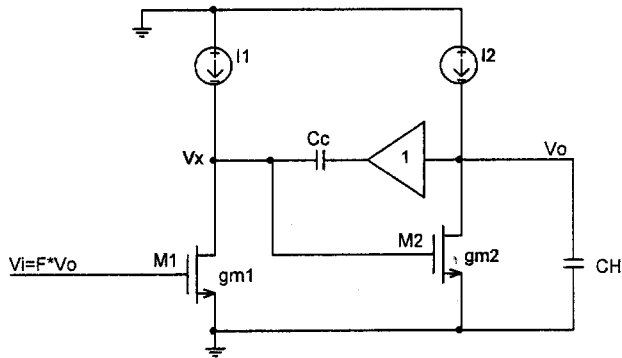
Calculate the minimum cutoff frequency  $f_T$  required for the sampling transistor for a 50MHz acquisition bandwidth and 20mV charge injection onto  $C_H$ . Assume worst-case conditions, i.e. that all channel charge is injected onto  $C_H$ .

Give both an algebraic expression and numerical value for the cutoff frequency.



## 2. Amplifier Output Noise

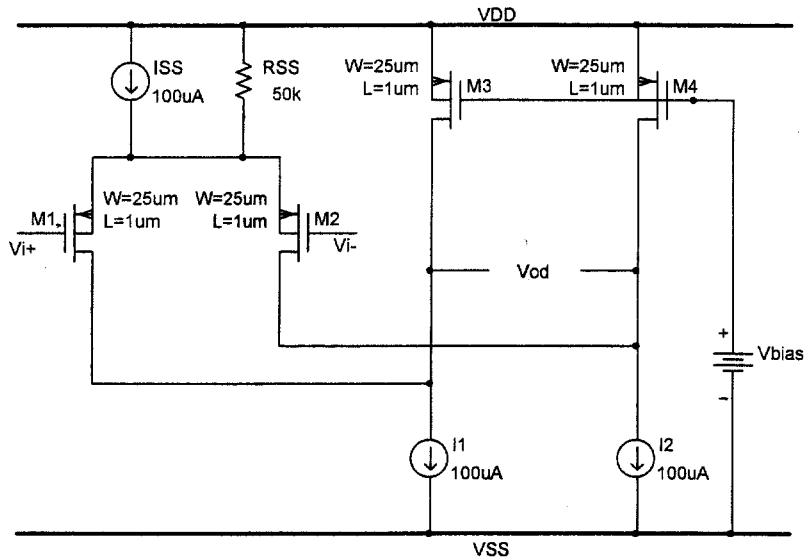
Derive an expression for the standard deviation of the noise voltage on node  $V_O$  (integrated over all frequencies) that is due to the thermal drain current noise from M2. Ignore all other noise sources, transistor output resistance, and all capacitors except  $C_C$  and  $C_L$ . The unity-gain buffer has the characteristics of an ideal source follower.



### 3. Power-Supply Rejection Ratio

Calculate the worst-case power supply rejection ratio (PSRR) at low frequency with respect to  $V_{DD}$  of the folded cascode shown below assuming a threshold voltage mismatch of  $10\text{mV}$  between all nominally matched pairs of transistors (i.e. M1-M2 and M3-M4). Assume  $V_{i+} = V_{i-}$ . The common-mode feedback circuit is not shown (but assume it's there). Give both an algebraic expression for the PSRR (in terms of  $g_m$ ,  $\Delta g_m$ ,  $R_{SS}$ ), and the numerical value.

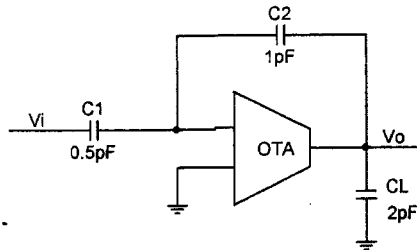
Assume  $V_{i+} = V_{i-}$ . The common-mode feedback circuit is not shown (but assume it's there). Give both an algebraic expression for the PSRR (in terms of  $g_m$ ,  $\Delta g_m$ ,  $R_{SS}$ ), and the numerical value.



#### 4. Settling Time

In the circuit shown below, capacitors  $C1$  and  $C2$  are discharged, then a 4V step is applied at the input  $V_i$ .

- What is the relative error of the output when all transients have died?
- Compute the settling time for 0.1% settling accuracy assuming infinite open-loop gain. Assume that the entire biasing current  $I_{SS}$  is available for slewing and that the transition between slewing and linear settling is abrupt.



Single-Stage  
OTA Specifications:

$$a_{vo} = 1000$$

$$g_{m1} = g_{m2} = 1\text{mS}$$

$$I_{SS} = 200\mu\text{A}$$

$$C_{in} = 1\text{pF}$$